

Inverter with Open Drain Output

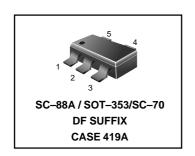
MC74VHC1G05

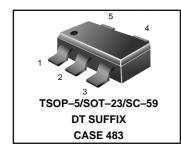
The MC74VHC1G05 is an advanced high speed CMOS inverter with open drain output fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including an open drain output which provides the capability to set output switching level. This allows the MC74VHC1G05 to be used to interface 5 V circuits to circuits of any voltage between V cc and 7 V using an external resistor and power supply.

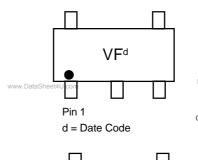
The MC74VHC1G05 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage.

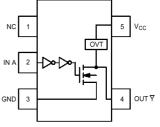
- High Speed: $t_{PD} = 3.8 \text{ ns}$ (Typ) at $V_{CC} = 5 \text{ V}$
- Low Internal Power Dissipation: I cc = 2 mA (Max) at T A = 25°C
- Power Down Protection Provided on Inputs
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FET = 105; Equivalent Gate = 26





MARKING DIAGRAMS





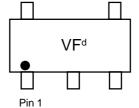




Figure 1. Pinout (Top View)

d = Date Code

Figure 2. Logic Symbol

PIN ASSIGNMENT						
1	NC					
2	IN A					
3	GND					
4 OUT \overline{Y}						

V_{cc}

FUNCTION TABLE

Inputs	Output
Α	Y
L	Z
Н	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.



MC74VHC1G05

MAXIMUM RATINGS (Note 1.)

Symbol	Parar	neter	Value	Unit
V _{cc}	DC Supply Voltage		- 0.5 to + 7.0	V
V IN	DC Input Voltage		- 0.5 to +7.0	V
V _{OUT}	DC Output Voltage		- 0.5 to +7.0	V
Lik	Input Diode Current		-20	mA
I _{OK}	Output Diode Current	V_{out} < GND; V_{out} > V_{cc}	+20	mA
I _{OUT}	DC Output Current, per Pin		+ 25	mA
I _{cc}	DC Supply Current, V cc and	GND	+50	mA
P _D	Power dissipation in still air	SC-88A, TSOP-5	200	mW
θ да	Thermal resistance	SC-88A, TSOP-5	333	°C/W
ΤL	Lead Temperature, 1 mm from	m Case for 10 s	260	°C
Τ _J	Junction Temperature Under	Bias	+ 150	°C
T stg	Storage temperature		-65 to +150	°C
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2)	>2000	V
		Machine Model (Note 3)	> 200	
		Charged Device Model (Note 4)	N/A	
I LATCH-UP	Latch-Up Performance Abo	ove V cc and Below GND at 125°C (Note 5)	± 500	mA

^{1.} Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

- 2. Tested to EIA/JESD22-A114-A
- 3. Tested to EIA/JESD22-A115-A
- 4. Tested to JESD22-C101-A
- 5. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit	
V _{cc}	DC Supply Voltage		2.0	5.5	V	
V _{IN}	DC Input Voltage		0.0	5.5	V	
V _{OUT}	DC Output Voltage		0.0	7.0	V	
T _A	Operating Temperature Range		– 55	+ 125	°C	
tr,tf	Input Rise and Fall Time	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	0	100	ns/V	
		$V_{CC} = 5.0 \pm 0.5 V$	0	20		

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction	Time,	Time,
Temperature °C	Hours	Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

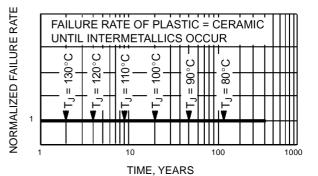


Figure 3. Failure Rate vs. Time Junction Temperature



MC74VHC1G05

DC ELECTRICAL CHARACTERISTICS

			V cc	Т	_A = 25	°C	T _A ≤	85 °C	-55°C≤	Γ _A ≤125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High-Level		2.0	1.5			1.5		1.5		V
	Input Voltage		3.0	2.1			2.1		2.1		
			4.5	3.15			3.15		3.15		
			5.5	3.85			3.85		3.85		
V _{IL}	Maximum Low-Level		2.0			0.5		0.5		0.5	V
	Input Voltage		3.0			0.9		0.9		0.9	
			4.5			1.35		1.35		1.35	
			5.5			1.65		1.65		1.65	
V _{OH}	Minimum High-Level	$V_{IN} = V_{IH} \text{ or } V_{IL}$	2.0	1.9	2.0		1.9		1.9		V
	Output Voltage	$I_{OH} = -50 \mu A$	3.0	2.9	3.0		2.9		2.9		
	$V_{IN} = V_{IH} \text{ or } V_{IL}$		4.5	4.4	4.0		4.4		4.4		
		$V_{IN} = V_{IH} \text{ or } V_{IL}$									Ī
		$I_{OH} = -4 \text{ mA}$	3.0	2.58			2.48		2.34		
		$I_{OH} = -8 \text{ mA}$	4.5	3.94			3.80		3.66		
V _{OL}	Maximum Low-Level	$V_{IN} = V_{IH} \text{ or } V_{IL}$	2.0		0.0	0.1		0.1		0.1	V
	Output Voltage	$I_{OL} = 50 \mu A$	3.0		0.0	0.1		0.1		0.1	
	$V_{IN} = V_{IH} \text{ or } V_{IL}$		4.5		0.0	0.1		0.1		0.1	
		$V_{IN} = V_{IH} \text{ or } V_{IL}$									Ī
		$I_{OL} = 4 \text{ mA}$	3.0			0.36		0.44		0.52	
		$I_{OL} = 8 \text{ mA}$	4.5			0.36		0.44		0.52	
I _{IN}	Maximum Input	$V_{IN} = 5.5 V \text{ or GND}$	0 to5.5			±0.1		±1.0		±1.0	μА
	Leakage Current										
I _{cc}	Maximum Quiescent	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	μΑ
	Supply Current										
I OPD	Maximum Off-state	V _{OUT} = 5.5 V	0			0.25		2.5		5.0	μА
	Leakage Current										

AC ELECTRICAL CHARACTERISTICS C $_{load}$ = 50 pF, Input t $_{r}$ = t $_{f}$ = 3.0 ns

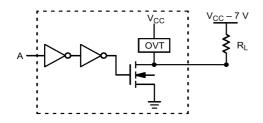
			Т	T _A = 25 °C		T _A ≤	85 °C	–55 °C t	o 125 °C	
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit
t PZL	Maximum Output	V CC = 3.3 ± 0.3 V C L = 15 pF		5.0	7.1		8.5		10.0	ns
	Enable Time, Input A to \overline{Y}	$R L = R I = 500 \Omega$ $C L = 50 pF$		7.5	10.6		12.0		14.5	
	Input A to Y	V CC = 5.0 ± 0.5 V C L = 15 pF		3.8	5.5		6.5		8.0	
		$R L = R I = 500 \Omega$ $C L = 50 pF$		5.3	7.5		8.5		10.0	
t PLZ	Maximum Output	$V CC = 3.3 \pm 0.3 V C L = 50 pF$		7.5	10.6		12.0		14.5	ns
	Disable Time	$R L = R I = 500 \Omega$								
		$V CC = 5.0 \pm 0.5 V C L = 50 pF$		5.3	7.5		8.5		10.0	
		R L = R I = 500 Ω								
C IN	Maximum Input			4	10		10		10	pF
	Capacitance									

		Typical @ 25°C, V_{cc} = 5.0 V	
C PD	Power Dissipation Capacitance (Note 6)	18	pF

^{6.} C $_{PD}$ is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD}XV_{CC}Xf_{in} + I_{CC}.C_{PD}$ is used to determine the noload dynamic power consumption; $P_D = C_{PD}XV_{CC}^2Xf_{in} + I_{CC}XV_{CC}$.



MC74VHC1G03



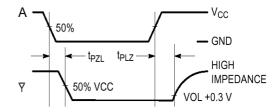
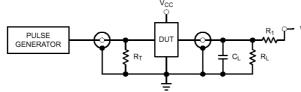


Figure 4. Output Voltage Mismatch Application

Figure 5. Switching Waveforms

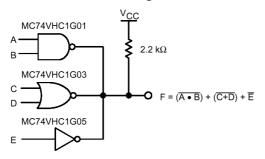


C L = 50 pF equivalent (Includes jig and probe capacitance)

R L = R 1 = 500Ω or equivalent

R T = Z OUT of pulse generator (typically 50 Ω)

Figure 6. Test Circuit



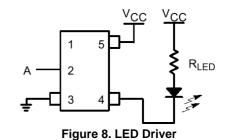


Figure 7. Complex Boolean Functions

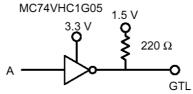


Figure 9. GTL Driver

DEVICE ORDERING INFORMATION

Device Nomenclature										
Device Order Number Logic Circuit		•		Device Package Function Suffix		Tape and Reel Suffix	Package Type (Name/SOT#/ Common Name)	Tape and Reel Size		
MC74VHC1G05DFT1	MC	74	VHC1G	05	DF	T1	SC-70/SC-88A/	178 mm (7 in)		
							SOT-353	3000 Unit		
MC74VHC1G05DFT2	MC	74	VHC1G	05	DF	T2	SC-70/SC-88A/	178 mm (7 in)		
							SOT-353	3000 Unit		
MC74VHC1G05DFT4	MC	74	VHC1G	05	DF	T4	SC-70/SC-88A/	330 mm (13 in)		
							SOT-353	10,000 Unit		
MC74VHC1G05DTT1	MC	74	VHC1G	05	DT	T1	SOT-23/TSOPS/	178 mm (7 in)		
							SC-59	3000 Unit		
MC74VHC1G05DTT3	MC	74	VHC1G	05	DT	T3	SOT-23/TSOPS/	330 mm (13 in)		
							SC-59	10,000 Unit		